

# L J Brillson

## List of Publications by Year in descending order

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191  
papers

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docs citations

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#	ARTICLE	IF	CITATIONS
1	Nanoscale interplay of native point defects near Sr-deficient Sr <sub>x</sub> TiO <sub>3</sub> /SrTiO <sub>3</sub> interfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, .	2.1	1
2	Optical and electronic effects of rapid thermal annealing at Irâ€“Ga <sub>2</sub> O <sub>3</sub> interfaces. Journal of Applied Physics, 2022, 131, .	2.5	1
3	Experimental determination of the valence band offsets of ZnGeN <sub>2</sub> and (ZnGe) <sub>0.94</sub> Ga <sub>0.12</sub> N <sub>2</sub> with GaN. Journal Physics D: Applied Physics, 2021, 54, 245102.	2.8	6
4	Depth-resolved cathodoluminescence and surface photovoltage spectroscopies of gallium vacancies in I <sup>2</sup> -Ga <sub>2</sub> O <sub>3</sub> with neutron irradiation and forming gas anneals. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2021, 39, .	1.2	5
5	Deep level defect spectroscopies of complex oxide surfaces and interfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	3
6	Cathodoluminescence and x-ray photoelectron spectroscopy of ScN: Dopant, defects, and band structure. APL Materials, 2020, 8, 081103.	5.1	7
7	Recovery from plasma etching-induced nitrogen vacancies in p-type gallium nitride using UV/O <sub>3</sub> treatments. Applied Physics Letters, 2020, 117, .	3.3	13
8	Elucidating Structural Transformations in Li <sub>x</sub> V <sub>2</sub> O <sub>5</sub> Electrochromic Thin Films by Multimodal Spectroscopies. Chemistry of Materials, 2020, 32, 7226-7236.	6.7	21
9	Nanoscale depth and lithiation dependence of V <sub>2</sub> O <sub>5</sub> band structure by cathodoluminescence spectroscopy. Journal of Materials Chemistry A, 2020, 8, 11800-11810.	10.3	10
10	Deep level defects and cation sublattice disorder in ZnGeN <sub>2</sub> . Journal of Applied Physics, 2020, 127, .	2.5	24
11	Direct, spatially resolved observation of defect states with electromigration and degradation of single crystal SrTiO <sub>3</sub> . Journal of Applied Physics, 2020, 127, .	2.5	7
12	Strain-driven disproportionation at a correlated oxide metal-insulator transition. Physical Review B, 2020, 101, .	3.2	26
13	Influence of Surface Chemistry on Water Absorption in Functionalized Germanane. Chemistry of Materials, 2020, 32, 1537-1544.	6.7	8
14	Neutron irradiation and forming gas anneal impact on I <sup>2</sup> -Ga <sub>2</sub> O <sub>3</sub> deep level defects. Journal Physics D: Applied Physics, 2020, 53, 465102.	2.8	14
15	Chemical migration and dipole formation at van der Waals interfaces between magnetic transition metal chalcogenides and topological insulators. Physical Review Materials, 2020, 4, .	2.4	4
16	Coherent growth and characterization of van der Waals $T\hat{\alpha}^2VSeZ\hat{\alpha}^2$ layers on GaAs(111)B using molecular beam epitaxy. Physical Review Materials, 2020, 4, .	2.4	2
17	Native Point Defect Measurement and Manipulation in ZnO Nanostructures. Materials, 2019, 12, 2242.	2.9	17
18	Direct observation of a two-dimensional hole gas at oxide interfaces. Nature Materials, 2018, 17, 231-236.	27.5	151

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19	Defect Characterization, Imaging, and Control in Wide-Bandgap Semiconductors and Devices. Journal of Electronic Materials, 2018, 47, 4980-4986.	2.2	7
20	Single Metal Ohmic and Rectifying Contacts to ZnO Nanowires: A Defect Based Approach. Annalen Der Physik, 2018, 530, 1700335.	2.4	13
21	Defect Manipulation To Control ZnO Micro-/Nanowire-Metal Contacts. Nano Letters, 2018, 18, 6974-6980.	9.1	17
22	Bandgap and band edge positions in compositionally graded ZnCdO. Journal of Applied Physics, 2018, 124, .	2.5	5
23	Identification of Ge vacancies as electronic defects in methyl- and hydrogen-terminated germanane. Applied Physics Letters, 2018, 113, 061110.	3.3	7
24	Topological Dirac semimetal Na <sub>3</sub> Bi films in the ultrathin limit via alternating layer molecular beam epitaxy. APL Materials, 2018, 6, 086103.	5.1	4
25	Optical signatures of deep level defects in Ga <sub>2</sub> O <sub>3</sub> . Applied Physics Letters, 2018, 112, .	3.3	113
26	Identification of a functional point defect in $\text{SrTiO}_3$ . Physical Review Materials, 2018, 2, .	2.4	14
27	Impact of defect distribution on IrO <sub>x</sub> /ZnO interface doping and Schottky barriers. Applied Physics Letters, 2017, 111, .	3.3	10
28	Uniform large-area growth of nanotemplated high-quality monolayer MoS <sub>2</sub> . Applied Physics Letters, 2017, 110, 263103.	3.3	8
29	Direct measurement of defect and dopant abruptness at high electron mobility ZnO homojunctions. Applied Physics Letters, 2016, 109, .	3.3	6
30	Native point defect formation in flash sintered ZnO studied by depth-resolved cathodoluminescence spectroscopy. Journal of Applied Physics, 2016, 120, .	2.5	24
31	Tailoring the Electronic Structure of Covalently Functionalized Germanane via the Interplay of Ligand Strain and Electronegativity. Chemistry of Materials, 2016, 28, 8071-8077.	6.7	71
32	Defect segregation and optical emission in ZnO nano- and microwires. Nanoscale, 2016, 8, 7631-7637.	5.6	47
33	Review of using gallium nitride for ionizing radiation detection. Applied Physics Reviews, 2015, 2, .	11.3	73
34	Native point defect energies, densities, and electrostatic repulsion across (Mg,Zn)O alloys. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1448-1454.	1.8	3
35	Direct correlation and strong reduction of native point defects and microwave dielectric loss in air-annealed (Ba,Sr)TiO <sub>3</sub> . Applied Physics Letters, 2015, 106, .	3.3	3
36	Near-nanoscale-resolved energy band structure of LaNiO <sub>3</sub> /La <sub>2</sub> /3Sr <sub>1</sub> /3MnO <sub>3</sub> /SrTiO <sub>3</sub> heterostructures and their interfaces. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, 04E103.	1.2	10

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37	Impact of Mg content on native point defects in Mg <sub>x</sub> Zn <sub>1-x</sub> O (0 ≤ x ≤ 0.56). APL Materials, 2015, 3, 062801.	5.1	7
38	Neutron irradiation effects on metal-gallium nitride contacts. Journal of Applied Physics, 2014, 115, .	2.5	15
39	Optical identification of oxygen vacancy formation at SrTiO <sub>3</sub> /(Ba,Sr)TiO <sub>3</sub> heterostructures. Journal Physics D: Applied Physics, 2014, 47, 255303.	2.8	22
40	Interplay of dopants and native point defects in ZnO. Physica Status Solidi (B): Basic Research, 2013, 250, 2110-2113.	1.5	11
41	Electronic Structure of Tantalum Oxynitride Perovskite Photocatalysts. Chemistry of Materials, 2013, 25, 3337-3343.	6.7	144
42	Effect of reduced dimensionality on the optical band gap of SrTiO <sub>3</sub> . Applied Physics Letters, 2013, 102, .	3.3	52
43	Depth resolved studies of SrTiO <sub>3</sub> defects using x-ray excited optical luminescence and cathodoluminescence. Applied Physics Letters, 2013, 102, .	3.3	9
44	The effect of thermal reactor neutron irradiation on semi-insulating GaN. Radiation Effects and Defects in Solids, 2013, 168, 924-932.	1.2	6
45	Neutron irradiation effects on gallium nitride-based Schottky diodes. Applied Physics Letters, 2013, 103, .	3.3	23
46	Design of an ultrahigh vacuum transfer mechanism to interconnect an oxide molecular beam epitaxy growth chamber and an x-ray photoemission spectroscopy analysis system. Review of Scientific Instruments, 2013, 84, 065105.	1.3	5
47	Characterization of polishing induced defects and hydrofluoric acid passivation effect in ZnO. Applied Physics Letters, 2013, 103, .	3.3	10
48	Heterojunction band offsets and dipole formation at BaTiO <sub>3</sub> /SrTiO <sub>3</sub> interfaces. Journal of Applied Physics, 2013, 114, .	2.5	29
49	Role of native point defects and Ga diffusion on electrical properties of degenerate Ga-doped ZnO. Physica Status Solidi (B): Basic Research, 2013, 250, 2114-2117.	1.5	3
50	Strain and Temperature Dependence of Defect Formation at AlGaIn/GaN High-Electron-Mobility Transistors on a Nanometer Scale. IEEE Transactions on Electron Devices, 2012, 59, 2667-2674.	3.0	14
51	Secondary Ion Mass Spectrometry. , 2012, , 197-212.		0
52	Rutherford Backscattering Spectrometry. , 2012, , 183-196.		0
53	Adsorbate-Semiconductor Sensors. , 2012, , 365-382.		0
54	Particle-Solid Scattering. , 2012, , 147-168.		0

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55	Applications of depth-resolved cathodoluminescence spectroscopy. Journal Physics D: Applied Physics, 2012, 45, 183001.	2.8	65
56	Thermal process dependence of Li configuration and electrical properties of Li-doped ZnO. Applied Physics Letters, 2012, 100, 042107.	3.3	33
57	Native point defects at ZnO surfaces, interfaces and bulk films. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1566-1569.	0.8	16
58	Self-compensation in semiconductors: The Zn vacancy in Ga-doped ZnO. Physical Review B, 2011, 84, .	3.2	169
59	ZnO Schottky barriers and Ohmic contacts. Journal of Applied Physics, 2011, 109, .	2.5	622
60	Impact of ultrathin Al <sub>2</sub> O <sub>3</sub> diffusion barriers on defects in high-k LaLuO <sub>3</sub> on Si. Applied Physics Letters, 2011, 98, 172902.	3.3	21
61	Nanoscale depth-resolved electronic properties of SiO <sub>2</sub> /SiO <sub>x</sub> /SiO <sub>2</sub> for device-tolerant electronics. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 011027.	1.2	4
62	Impact of ultrathin Al <sub>2</sub> O <sub>3</sub> barrier layer on electrical properties of LaLuO <sub>3</sub> metal-oxide-semiconductor devices. Applied Physics Letters, 2011, 98, 122907.	3.3	12
63	Field-induced strain degradation of AlGaIn/GaN high electron mobility transistors on a nanometer scale. Applied Physics Letters, 2010, 97, .	3.3	9
64	Defects at oxygen plasma cleaned ZnO polar surfaces. Journal of Applied Physics, 2010, 108, .	2.5	29
65	X-ray photoemission spectroscopy of Sr <sub>2</sub> FeMoO <sub>6</sub> film stoichiometry and valence state. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 1240-1244.	2.1	11
66	Vacancy defect and defect cluster energetics in ion-implanted ZnO. Physical Review B, 2010, 81, .	3.2	121
67	Depth-resolved subsurface defects in chemically etched SrTiO <sub>3</sub> . Applied Physics Letters, 2009, 94, .	3.3	36
68	Metal contacts on bulk ZnO crystal treated with remote oxygen plasma. Journal of Vacuum Science & Technology B, 2009, 27, 1774.	1.3	7
69	Surface, bulk, and interface electronic states of epitaxial BiFeO <sub>3</sub> films. Journal of Vacuum Science & Technology B, 2009, 27, 2012-2014.	1.3	17
70	Nanoscale mapping of temperature and defect evolution inside operating AlGaIn/GaN high electron mobility transistors. Applied Physics Letters, 2009, 95, .	3.3	25
71	Polarity-related asymmetry at ZnO surfaces and metal interfaces. Journal of Vacuum Science & Technology B, 2009, 27, 1710.	1.3	15
72	Nanoscale depth-resolved electronic properties of SiO <sub>2</sub> /SiO <sub>x</sub> /SiO <sub>2</sub> gate dielectrics for radiation-tolerant electronics. , 2009, , .		0

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73	Impact of near-surface defects and morphology on ZnO luminescence. Applied Physics Letters, 2009, 94, .	3.3	20
74	Detection of clinically relevant levels of protein analyte under physiologic buffer using planar field effect transistors. Biosensors and Bioelectronics, 2008, 24, 505-511.	10.1	50
75	Characterization of electronic structure and defect states of thin epitaxial BiFeO <sub>3</sub> films by UV-visible absorption and cathodoluminescence spectroscopies. Applied Physics Letters, 2008, 92, .	3.3	176
76	Impact of near-surface native point defects, chemical reactions, and surface morphology on ZnO interfaces. Journal of Vacuum Science & Technology B, 2008, 26, 1477-1482.	1.3	11
77	Atomic diffusion and interface electronic structure at In <sub>0.49</sub> Ga <sub>0.51</sub> P/GaAs heterojunctions. Journal of Vacuum Science & Technology B, 2008, 26, 89.	1.3	4
78	Depth-resolved cathodoluminescence spectroscopy study of defects in SrTiO <sub>3</sub> . Journal of Vacuum Science & Technology B, 2008, 26, 1466-1471.	1.3	26
79	Surface traps in vapor-phase-grown bulk ZnO studied by deep level transient spectroscopy. Journal of Applied Physics, 2008, 104, .	2.5	23
80	Electrical Detection of Biological Conjugation by AlGaN/GaN Heterostructure Field Effect Transistors. , 2008, , .		0
81	Zn- and O-face polarity effects at ZnO surfaces and metal interfaces. Applied Physics Letters, 2008, 93, 072111.	3.3	58
82	Application of high spatial resolution scanning work function spectroscopy to semiconductor surfaces and interfaces. Journal of Vacuum Science & Technology B, 2007, 25, 334.	1.3	4
83	Atomic diffusion and electronic structure in Al <sub>0.52</sub> In <sub>0.48</sub> P/GaAs heterostructures. Journal of Vacuum Science & Technology B, 2007, 25, 1916.	1.3	1
84	Role of subsurface defects in metal-ZnO(0001) Schottky barrier formation. Journal of Vacuum Science & Technology B, 2007, 25, 1405.	1.3	28
85	Process-dependent defects in Si <sup>+</sup> /HfO <sub>2</sub> /Mo gate oxide heterostructures. Applied Physics Letters, 2007, 90, 052901.	3.3	40
86	Process-dependent electronic states at Mo/hafnium oxide/Si interfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 1261-1266.	2.1	0
87	Inhomogeneities in Ni <sup>+</sup> /4H-SiC Schottky barriers: Localized Fermi-level pinning by defect states. Journal of Applied Physics, 2007, 101, 114514.	2.5	80
88	Interface bonding, chemical reactions, and defect formation at metal-semiconductor interfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 943-949.	2.1	21
89	Thermally driven defect formation and blocking layers at metal-ZnO interfaces. Applied Physics Letters, 2007, 91, .	3.3	41
90	Dominant effect of near-interface native point defects on ZnO Schottky barriers. Applied Physics Letters, 2007, 90, 102116.	3.3	144

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91	Role of Interface Layers and Localized States in TiAl-Based Ohmic Contacts to p-Type 4H-SiC. Journal of Electronic Materials, 2007, 36, 277-284.	2.2	32
92	On microscopic compositional and electrostatic properties of grain boundaries in polycrystalline $\text{CuIn}_{1-x}\text{Ga}_x\text{Se}_2$ . Journal of Vacuum Science & Technology B, 2006, 24, 1739.	1.3	14
93	Compositional modulation and optical emission in AlGaIn epitaxial films. Journal of Applied Physics, 2006, 100, 103512.	2.5	57
94	Thermal Stability of Defects in Substrates for Multiferroic Materials. Materials Research Society Symposia Proceedings, 2006, 966, 1.	0.1	0
95	Low Energy CL Spectroscopy of Interfaces and Nanostructures. Microscopy and Microanalysis, 2006, 12, 172-173.	0.4	0
96	Schottky barrier formation at nonpolar Au/GaN epilayer interfaces. Journal of Electronic Materials, 2006, 35, 581-586.	2.2	4
97	Nanoscale Deep Level Defect Correlation with Schottky Barriers in 4H-SiC/Metal Diodes. Materials Science Forum, 2006, 527-529, 907-910.	0.3	0
98	A Study of Inhomogeneous Schottky Diodes on n-Type 4H-SiC. Materials Science Forum, 2006, 527-529, 911-914.	0.3	1
99	Characterization of Ti/Al Ohmic Contacts to p-Type 4H-SiC Using Cathodoluminescence and Auger Electron Spectroscopies. Materials Science Forum, 2006, 527-529, 891-894.	0.3	1
100	Controlled gate surface processing of AlGaIn-GaN high electron mobility transistors. Applied Physics Letters, 2006, 89, 183523.	3.3	4
101	Local electronic and chemical structure at GaN, AlGaIn and SiC heterointerfaces. Applied Surface Science, 2005, 244, 257-263.	6.1	2
102	Selection and characteristics of peptides that bind thermally grown silicon dioxide films. New Biotechnology, 2005, 22, 201-204.	2.7	55
103	Shallow donor generation in ZnO by remote hydrogen plasma. Journal of Electronic Materials, 2005, 34, 399-403.	2.2	12
104	Atomic diffusion and band lineups at $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ -on-InP heterointerfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1832.	1.6	11
105	Electronic defect states at annealed metal-SiC interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 594.	1.6	7
106	Defect-driven inhomogeneities in Ni-SiC Schottky barriers. Applied Physics Letters, 2005, 87, 242106.	3.3	45
107	Direct observation of copper depletion and potential changes at copper indium gallium diselenide grain boundaries. Applied Physics Letters, 2005, 86, 162105.	3.3	129
108	Spontaneous compositional superlattice and band-gap reduction in Si-doped $\text{Al}_x\text{Ga}_{1-x}\text{N}$ epilayers. Applied Physics Letters, 2005, 87, 191906.	3.3	22

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109	Pre-metallization processing effects on Schottky contacts to AlGaIn-GaN heterostructures. Journal of Applied Physics, 2005, 97, 084502.	2.5	16
110	Evidence of interface-induced persistent photoconductivity in InP-In <sub>0.53</sub> Ga <sub>0.47</sub> As-InP double heterostructures grown by molecular-beam epitaxy. Applied Physics Letters, 2005, 87, 032106.	3.3	1
111	Role of near-surface states in ohmic-Schottky conversion of Au contacts to ZnO. Applied Physics Letters, 2005, 87, 012102.	3.3	233
112	Remote hydrogen plasma doping of single crystal ZnO. Applied Physics Letters, 2004, 84, 2545-2547.	3.3	124
113	Micro-Auger electron spectroscopy studies of chemical and electronic effects at GaN-sapphire interfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 2284-2289.	2.1	3
114	Origins of luminescence from nitrogen-ion-implanted epitaxial GaAs. Applied Physics Letters, 2004, 85, 2774-2776.	3.3	4
115	Atomic layer diffusion and electronic structure at In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 554.	1.6	14
116	Surface cleaning and annealing effects on Ni-AlGaIn interface atomic composition and Schottky barrier height. Applied Physics Letters, 2004, 85, 1368-1370.	3.3	35
117	Remote hydrogen plasma processing of ZnO single crystal surfaces. Journal of Applied Physics, 2003, 94, 4256-4262.	2.5	71
118	Influence of oxygen on luminescence and vibrational spectra of Mg-doped GaN. Physica Status Solidi (B): Basic Research, 2003, 240, 356-359.	1.5	5
119	Effects of deep-level defects on ohmic contact and frequency performance of AlGaIn/GaN high-electron-mobility transistors. Applied Physics Letters, 2003, 83, 485-487.	3.3	11
120	Origin and microscopic mechanism for suppression of leakage currents in Schottky contacts to GaN grown by molecular-beam epitaxy. Journal of Applied Physics, 2003, 94, 7611.	2.5	37
121	Deep level defects and doping in high Al mole fraction AlGaIn. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 2558.	1.6	47
122	Thermal and doping dependence of 4H-SiC polytype transformation. Applied Physics Letters, 2002, 81, 2785-2787.	3.3	32
123	Detection of trap activation by ionizing radiation in SiO <sub>2</sub> by spatially localized cathodoluminescence spectroscopy. Journal of Applied Physics, 2002, 92, 5729-5734.	2.5	9
124	Microcathodoluminescence spectroscopy of defects in Bi <sub>2</sub> O <sub>3</sub> -doped ZnO grains. Journal of Applied Physics, 2002, 92, 5072-5076.	2.5	7
125	Depth-dependent investigation of defects and impurity doping in GaN/sapphire using scanning electron microscopy and cathodoluminescence spectroscopy. Journal of Applied Physics, 2002, 91, 6729.	2.5	41
126	Simultaneous observation of luminescence and dissociation processes of Mg-H complex for Mg-doped GaN. Journal of Applied Physics, 2002, 92, 3657-3661.	2.5	25



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127	Chemically dependent traps and polytypes at Pt/Ti contacts to 4H and 6H-SiC. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 554.	1.6	13
128	Effect of Remote Hydrogen Plasma Treatment on ZnO Single Crystal Surfaces. Materials Research Society Symposia Proceedings, 2002, 744, 1.	0.1	3
129	Characterization of 1.8-MeV proton-irradiated AlGaIn/GaN field-effect transistor structures by nanoscale depth-resolved luminescence spectroscopy. IEEE Transactions on Nuclear Science, 2002, 49, 2695-2701.	2.0	33
130	Si doping of high-Al-mole fraction Al <sub>x</sub> Ga <sub>1-x</sub> N alloys with rf plasma-induced molecular-beam-epitaxy. Applied Physics Letters, 2002, 81, 5192-5194.	3.3	32
131	Role of barrier and buffer layer defect states in AlGaIn/GaN HEMT structures. Journal of Electronic Materials, 2001, 30, 123-128.	2.2	17
132	Nanoscale luminescence spectroscopy of defects at buried interfaces and ultrathin films. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1762.	1.6	81
133	Observation of 4H-SiC to 3C-SiC polytypic transformation during oxidation. Applied Physics Letters, 2001, 79, 3056-3058.	3.3	148
134	Analysis of tunneling magnetoresistance test structures by low energy electron nanoscale-luminescence spectroscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2001, 19, 1199-1202.	2.1	1
135	Low energy electron excited nanoscale luminescence spectroscopy of erbium doped AlN. Journal of Electronic Materials, 2000, 29, 311-316.	2.2	4
136	Luminescence spectroscopy of GaN in the high-temperature regime from room temperature to 900°C. Applied Physics Letters, 2000, 77, 699-701.	3.3	26
137	Low-energy cathodoluminescence spectroscopy of erbium-doped gallium nitride surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 3437-3442.	2.1	5
138	Localized states at InGaIn/GaN quantum well interfaces. Applied Physics Letters, 1999, 75, 3835-3837.	3.3	41
139	Electronic near-surface defect states of bare and metal covered n-GaN films observed by cathodoluminescence spectroscopy. Journal of Electronic Materials, 1999, 28, 308-313.	2.2	13
140	Ultrathin Silicon Oxide and Nitride - Silicon Interface States. Materials Research Society Symposia Proceedings, 1999, 567, 549.	0.1	3
141	Cathodoluminescence measurements of suboxide band-tail and Si dangling bond states at ultrathin Si/SiO <sub>2</sub> interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2177.	1.6	5
142	Depth-dependent spectroscopic defect characterization of the interface between plasma-deposited SiO <sub>2</sub> and silicon. Applied Physics Letters, 1998, 73, 791-793.	3.3	36
143	Cathodoluminescence Deep Level Spectroscopy of Etched and In-Situ Annealed 6H-SiC. Materials Research Society Symposia Proceedings, 1998, 512, 137.	0.1	0
144	Deep Level Characterization of Interface-Engineered ZnSe Layers Grown by Molecular Beam Epitaxy on GaAs. Materials Research Society Symposia Proceedings, 1998, 535, 77.	0.1	1

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145	Luminescence measurements of sub-oxide band-tail and Si dangling bond states at ultrathin. , 1998, , .		0
146	Atomic diffusion-induced deep levels near ZnSe/GaAs(100) interfaces. Applied Physics Letters, 1995, 66, 3301-3303.	3.3	36
147	Geometric ordering, surface chemistry, band bending, and work function at decapped GaAs(100) surfaces. Physical Review B, 1992, 46, 13293-13302.	3.2	63
148	Process-Dependent Electronic Structure at Metallized GaAs Contacts. Materials Research Society Symposia Proceedings, 1992, 260, 449.	0.1	0
149	Increased range of Fermi-level stabilization energy at metal/melt-grown GaAs(100) interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 2129.	1.6	17
150	Correlation of deep-level and chemically-active-site densities at vicinal GaAs(100)-Al interfaces. Physical Review B, 1991, 44, 1391-1394.	3.2	11
151	Orientation-dependent chemistry and Schottky-barrier formation at metal-GaAs interfaces. Physical Review Letters, 1990, 64, 2551-2554.	7.8	51
152	Confirmation of the temperature-dependent photovoltaic effect on Fermi-level measurements by photoemission spectroscopy. Physical Review B, 1990, 41, 12299-12302.	3.2	43
153	Temperature-dependent formation of interface states and Schottky barriers at metal/molecular-beam epitaxy GaAs(100) junctions. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 3803-3808.	2.1	9
154	Band bending and interface states for metals on GaAs. Applied Physics Letters, 1988, 52, 2052-2054.	3.3	45
155	Arsenic- and metal-induced GaAs interface states by low-energy cathodoluminescence spectroscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 1397.	1.6	26
156	Cathodoluminescence spectroscopy of metal-semiconductor interface structures. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1988, 6, 1437-1445.	2.1	27
157	Interfacial deep-level formation and its effect on band bending at metal/CdTe interfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1988, 6, 2752-2756.	2.1	13
158	Near-ideal Schottky barrier formation at metal-GaP interfaces. Applied Physics Letters, 1987, 50, 1379-1381.	3.3	34
159	Optical emission properties of metal/InP and GaAs interface states. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1987, 5, 1516-1520.	2.1	8
160	Optical-Emission Properties of Interface States for Metals on III-V Semiconductor Compounds. Physical Review Letters, 1986, 57, 487-490.	7.8	53
161	Absence of Fermi level pinning at metal-InxGa1-xAs(100) interfaces. Applied Physics Letters, 1986, 48, 1458-1460.	3.3	31
162	Cathodoluminescence spectroscopy studies of laser-annealed metal-semiconductor interfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1985, 3, 1011-1015.	2.1	22

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164	Photoemission studies of atomic redistribution at gold-silicon and aluminum-silicon interfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1984, 2, 551-555.	2.1	45
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